

MvpLED™ SL-M-B45AC

High Power BLUE LED

BLUE LED

Introduction

The advantages of the patented and proprietary MvpLED™ design especially in Thermal management, and Optical efficacy, are realized in light quality, lifetime, color consistency, reliability and overall efficiency of the luminaire. Available in UV, Violet, Blue and Green, SemiLEDs high efficiency chips bring real benefits to any lamp or luminaire manufacturer.

Copper alloy, used in SemiLEDs MvpLED™ chips, is a better conductor of heat than any other material on the market used in the fabrication of LEDs. This is a major advantage for any lamp or luminaire manufacturer. No matter how good a thermal design is, if the contact material to the junction is a poor conductor then the cooling effects of the heat-sink are significantly reduced.

Using a proprietary surface texturing technique, SemiLEDs LEDs maximize light extraction and efficiency. Coupled with the lack of Sapphire and a 90% efficient Reflective Layer, SemiLEDs chips exhibit an almost perfect Lambertian radiation pattern.

SemiLEDs' patented and unique process consumes no Sapphire, significantly reducing the Carbon footprint. The lack of a Sapphire base also removes a thermal management bottleneck while providing the most environmentally friendly LED on the market.

RoHS and REACH Compliant

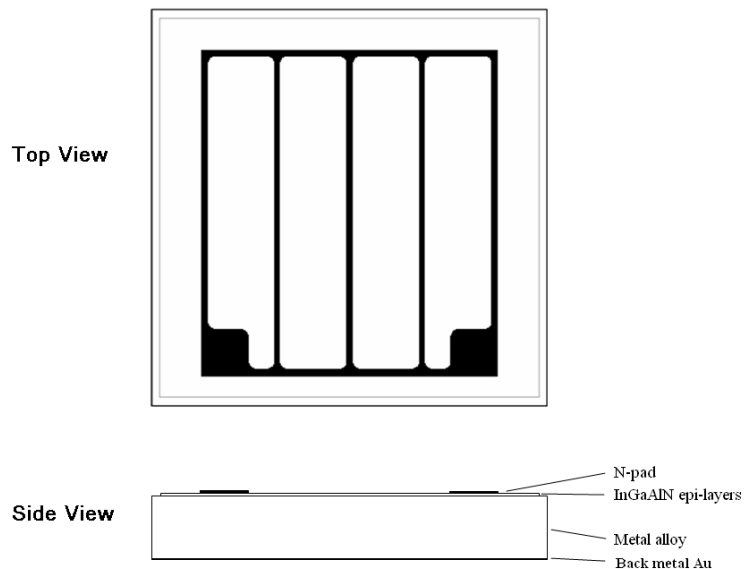
Feature

Metal alloy device-----	Low cost high thermal conductivity
Thickness 145 μm -----	Consolidated metal alloy
P-N junction high at 140 μm -----	Silver epoxy die attachment compatible
One pad structure-----	Low package cost
Nearly Perfect Lambert an emission pattern -----	Ideal for white light design
Patterned surface -----	Maximum light extraction

Applications

LCD backlight
 Digital Camera Flash light
 High Power LED
 Automotive lighting
 Signalling
 Signage
 Miniature Light Engine

Chip Mechanical Diagram



Mechanical Specifications

P-N junction area	1050 μm X 1050 μm	$\pm 20 \mu\text{m}$
Base area	1200 μm X 1200 μm	$\pm 50 \mu\text{m}$
Chip thickness	145 μm	$\pm 15 \mu\text{m}$
Bond pad size	140 μm	$\pm 15 \mu\text{m}$
Bond pad thickness	2.5 μm	$\pm 0.5 \mu\text{m}$
Junction height	140 μm	$\pm 15 \mu\text{m}$

Optical and Electrical Characteristics at 350mA, Ta at 25°C

Parameter	Symbol	Min	Typ	Max	Remark
Forward voltage:	Vf		3.1	3.3	Volt
Spectra half width	$\Delta\lambda$		20	40	nm
Reverse current	Ir			2 μ A	Vr= 5 Volt

Measured by SemiLEDs on bare chip

Absolute Maximum Ratings, Ta at 25°C

Forward Current (DC)	500 mA
Peak Forward Current (1/10 duty cycle @ 1KHz)	800 mA
LED Junction Temperature	125°C
Reverse Voltage	5 V
Operating Temperature	-40°C to +110°C
Storage Temperature	-40°C to +110°C
Temperature during packaging (reflow)	280°C < 10 sec

Maximum ratings are strongly package dependent and may differ between different packaged devices. The values given were collected by SemiLEDs' in-house package.

BIN Table (Output Power at 350mA, Ta at 25°C)

Wd Range(nm)	400-450mW	450-500mW	500-550mW	550-600mW
450-452.5	AG	AH	AI	AJ
452.5-455	BG	BH	BI	BJ
455-457.5	CG	CH	CI	CJ
457.5-460	DG	DH	DI	DJ
460-462.5	EG	EH	EI	EJ
462.5-465	FG	FH	FI	FJ
465-467.5	GG	GH	GI	
467.5-470	HG	HH	HI	
470-472.5	IG	IH	II	
472.5-475	JG	JH	JI	

Performance Diagram

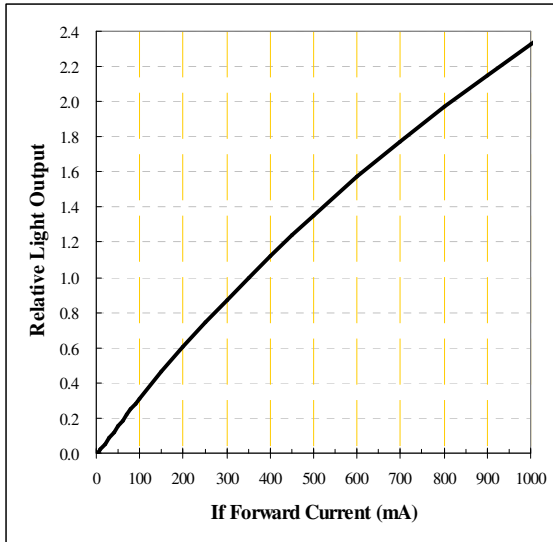


Fig-1 Relative Light Output vs. Forward Current.

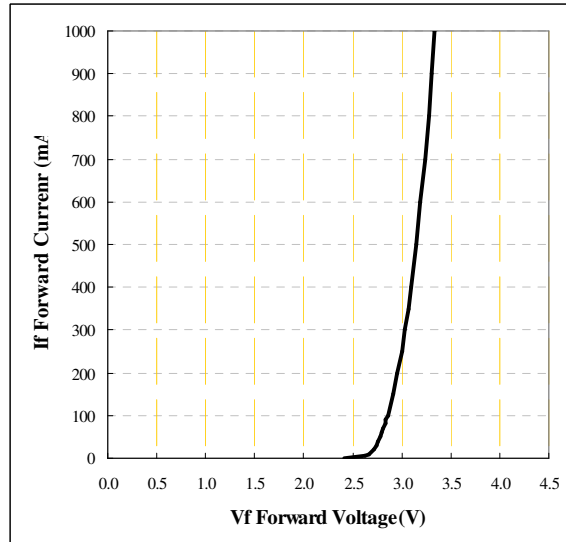


Fig-2 Forward Current vs. Forward Voltage.

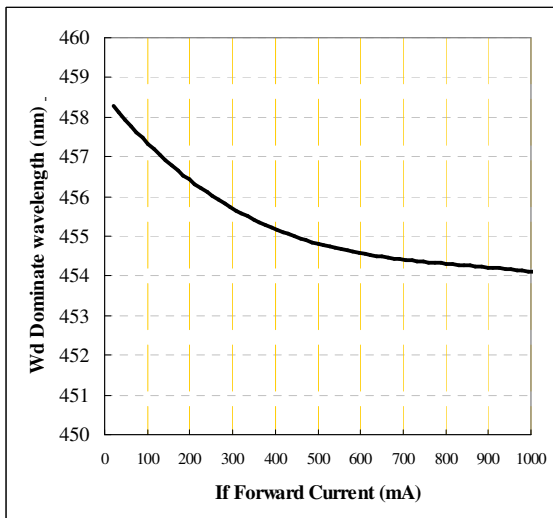


Fig-3 Dominate Wavelength vs. Forward Current.

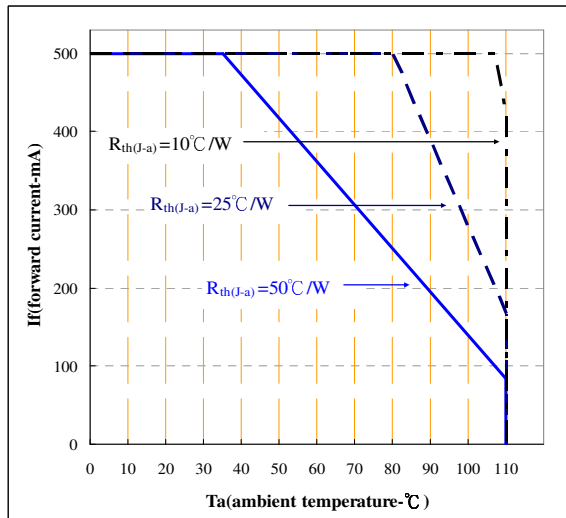


Fig-4 Maximum Driving Forward DC Current vs. Ambient Temperature.

Note:

- Minimum and maximum value refers to the limits and set up of SemiLEDs' testers. All other measurement data are defined as long-term production mean values and are only given for information.
- A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system. Life support devices or systems are intended (i) to be implanted in the human body, or (ii) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered. Components used as a critical component must be approved in writing by SemiLEDs.

About Us

SemiLEDs is a US based manufacturer of ultra-high bright LED chips with state of the art fabrication facilities in Hsinchu Science Park, Taiwan. SemiLEDs specializes in the development and manufacturing of metal alloy vertical LED chips in blue (white), green and UV using our patented and proprietary MvpLED™ technology. This unique design allows for higher performance and longer lumen maintenance. SemiLEDs new high power I-core MvpLEDs can deliver 120lm/W. In December 2008 The World Economic Forum recognized SemiLEDs' innovations with the 2009 Technology Pioneer Award.



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